

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
14 July 2005 (14.07.2005)

PCT

(10) International Publication Number
WO 2005/064687 A1

(51) International Patent Classification⁷: **H01L 29/861**,
21/329, 21/225

Erwin, A. [NL/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).

(21) International Application Number:
PCT/IB2004/052864

(74) Agents: **ELEVELD, Koop, J.** et al.; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).

(22) International Filing Date:
20 December 2004 (20.12.2004)

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
03104933.1 23 December 2003 (23.12.2003) EP
04103461.2 20 July 2004 (20.07.2004) EP

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(71) Applicant (for all designated States except US): **KONINKLIJKE PHILIPS ELECTRONICS N.V.** [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(72) Inventors; and

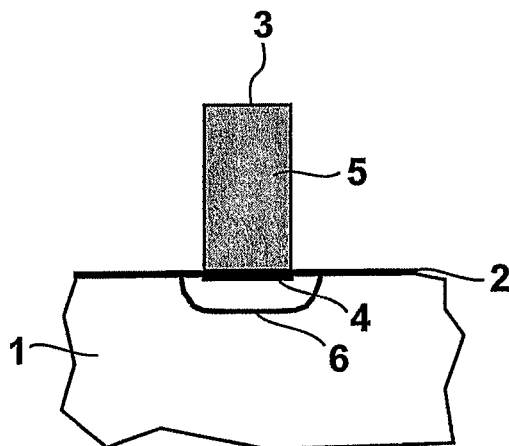
(75) Inventors/Applicants (for US only): **HURKX, Godefridus, A., M.** [NL/NL]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **AGARWAL, Prabhat** [DE/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **BALKENENDE, Abraham, R.** [NL/NL]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **MAGNEE, Petrus, H., C.** [NL/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **WAGEMANS, Melanie, M., H.** [NL/NL]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **BAKKERS, Erik, P., A., M.** [NL/NL]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **HIJZEN,**

Declaration under Rule 4.17:

— as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY,

[Continued on next page]

(54) Title: SEMICONDUCTOR DEVICE COMPRISING A PN-HETEROJUNCTION



(57) Abstract: An electric device is disclosed comprising a pn-heterojunction (4) formed by a nanowire (3) of 111-V semiconductor material and a semiconductor body (1) comprising a group IV semiconductor material. The nanowire (3) is positioned in direct contact with the surface (2) of the semiconductor body (1) and has a first conductivity type, the semiconductor body (1) has a second conductivity type opposite to the first conductivity type, the nanowire (3) forming with the semiconductor body (1) a pn-heterojunction (4). The nanowire of III-V semiconductor material can be used as a diffusion source (5) of dopant atoms into the semiconductor body. The diffused group III atoms and/or the group V atoms from the III-V material are the dopant atoms forming a region (6) in the semiconductor body in direct contact with the nanowire (3).

WO 2005/064687 A1



TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

Published:

— *with international search report*